

n-channel JFETs designed for . . .



Performance Curves NRL
See Section 5

- **Small-Signal Amplifiers**
- **Oscillators**

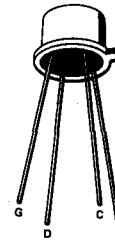
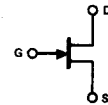
BENEFITS

- Operates from High Supply Voltages
 $BV_{GSS} > 50 \text{ V}$

***ABSOLUTE MAXIMUM RATINGS (25°C)**

Gate-Drain or Gate-Source Voltage (Note 1)	-50 V
Gate Current	10 mA
Total Device Dissipation at (or below) 25°C		
Free-Air Temperature (Note 2)	300 mW
Storage Temperature Range	-65 to +200°C
Lead Temperature		
(1/16" from case for 10 seconds)	300°C

TO-72
See Section 7



***ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)**

Characteristic	2N3821		2N3822		Unit	Test Conditions		
	Min	Max	Min	Max				
1 2 S T A T I C	IGSS	Gate Reverse Current		-0.1		nA	VGS = -30 V, VDS = 0 150°C	
				-0.1		-0.1		µA
3	BVGSS	Gate-Source Breakdown Voltage	-50		-50		V IG = -1 µA, VDS = 0 VDS = 15 V, ID = 0.5 nA VDS = 15 V, ID = 50 µA VDS = 15 V, ID = 200 µA	
4	VGS(off)	Gate-Source Cutoff Voltage			-4			
5	VGS	Gate-Source Voltage	-0.5		-2			
					-1	-4		
6	IDSS	Saturation Drain Current (Note 3)	0.5	2.5	2	10	mA VDS = 15 V, VGS = 0	
7	gfs	Common-Source Forward Transconductance (Note 3)	1500	4500	3000	6500	µmho VDS = 15 V, VGS = 0	f = 1 kHz
8	yfs	Common-Source Forward Transmittance	1500		3000			f = 100 MHz
9	gos	Common-Source Output Conductance (Note 3)		10		20		f = 1 kHz
10	Ciss	Common-Source Input Capacitance		6		6		pF f = 1 MHz
11	Crss	Common-Source Reverse Transfer Capacitance		3		3		
12	NF	Noise Figure		5		5	dB VDS = 15 V, VGS = 0, Rgen = 1 meg, BW = 5 Hz f = 10 Hz	
13	en	Equivalent Short-Circuit Input Noise Voltage		200		200		nV/√Hz VDS = 15 V, VGS = 0, BW = 5 Hz

*JEDEC Registered Data.

NRL

NOTES:

1. Due to symmetrical geometry, these units may be operated with source and drain leads interchanged.
2. Derate linearly to 175°C free-air temperature at rate of 2 mW/°C.
3. These parameters are measured during a 2 msec interval 100 msec after d-c power is applied.

2N3821 2N3822

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Siliconix